

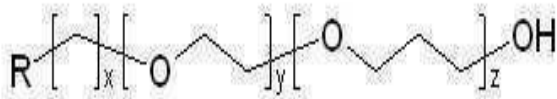
ABSTRACT

CLEANING COMPOSITION FOR PHOTOLITHOGRAPHY AND METHOD OF FORMING PHOTORESIST PATTERN USING THE SAME

5

Disclosed are a cleaning composition for photolithography and a method of forming a photoresist pattern using the same. The cleaning composition, necessary for forming a photoresist pattern having a high aspect ratio, includes water and a
10 compound represented by Chemical Formula 1 below:

[Chemical Formula 1]



wherein R is H or OH, x is an integer selected from 1 to 100, y is an integer selected from 0 to 100, and z is an
15 integer selected from 0 to 100. This cleaning composition is useful for forming a pattern using any of a variety of light sources, and also, even when it is difficult to form a fine pattern as desired using a photoresist alone, a fine pattern can be realized at a desired level of fineness and production
20 costs can be reduced.

[FIG. 1]